# <u>TOSHIBA</u>

TOSHIBA Field Effect Transistor Silicon N Channel MOS Type (U-MOSIV)

# **TPC6011**

#### Notebook PC Applications Portable Equipment Applications

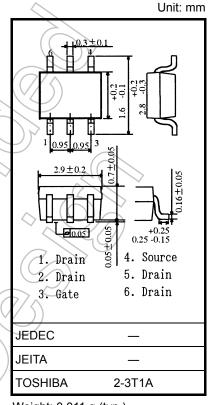
• Low drain-source ON-resistance:  $R_{DS}$  (ON) = 16 m $\Omega$  (typ.)

$$(V_{GS} = 10V)$$

- Low leakage current:  $I_{DSS} = 10 \ \mu A \ (max) \ (V_{DS} = 30 \ V)$
- Enhancement mode:  $V_{th}$  = 1.3 to 2.5 V ( $V_{DS}$  = 10 V,  $I_D$  = 1 mA)

	•	-	-	AL	
Characteristics	Symbol	Rating	Unit	$\langle \rangle$	
Drain-source voltage		V <sub>DSS</sub>	30	$((\underline{v}))$	
Drain-gate voltage ( $R_{GS} = 20 \text{ k}\Omega$ )		V <sub>DGR</sub>	30	V	
Gate-source voltage	V <sub>GSS</sub>	±20	V		
Drain current	DC (Note 1)	ID	6	A	
	Pulse (Note 1)	I <sub>DP</sub>	24	A	
Drain power dissipation	(t = 5 s) (Note 2a)	PD	2.2	W	
Drain power dissipation	(t = 5 s) (Note 2b)	PD	0.7	w	$\rangle \rangle$
Single pulse avalanche ene	EAS	2.3	mJ		
Avalanche current	JAR	3	A		
Channel temperature	T <sub>ch</sub>	150	°C		
Storage temperature range	T <sub>stg</sub>	-55 to 150	°C		

#### Absolute Maximum Ratings (Ta = 25°C)



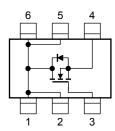
Weight: 0.011 g (typ.)

Note: Using continuously under heavy loads (e.g. the application of high temperature/current/voltage and the significant change in temperature, etc.) may cause this product to decrease in the reliability significantly even if the operating conditions (i.e. operating temperature/current/voltage, etc.) are within the absolute maximum ratings. Please design the appropriate reliability upon reviewing the Toshiba Semiconductor Reliability Handbook ("Handling Precautions"/"Derating Concept and Methods") and individual reliability data (i.e. reliability test report and estimated failure rate, etc).

### **Thermal Characteristics**

Characteristics	Symbol	Max	Unit
Thermal resistance, channel to ambient (t = 5 s) (Note 2a)	R <sub>th (ch-a)</sub>	56.8	°C/W
Thermal resistance, channel to ambient (t = 5 s) (Note 2b)	R <sub>th (ch-a)</sub>	178.5	°C/W

### **Circuit Configuration**

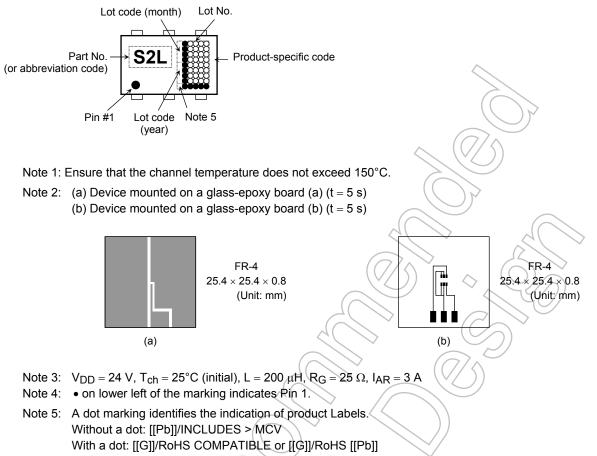


Note: (Note 1), (Note 2), (Note 3): See other pages.

This transistor is an electrostatic-sensitive device. Please handle with caution.

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#### Marking (Note 4)



Please contact your TOSHIBA sales representative for details as to environmental matters such as the RoHS compatibility of Product. The RoHS is the Directive 2011/65/EU of the European Parliament and of the Council of 8 June 2011 on the restriction of the use of certain hazardous substances in electrical and electronic equipment.

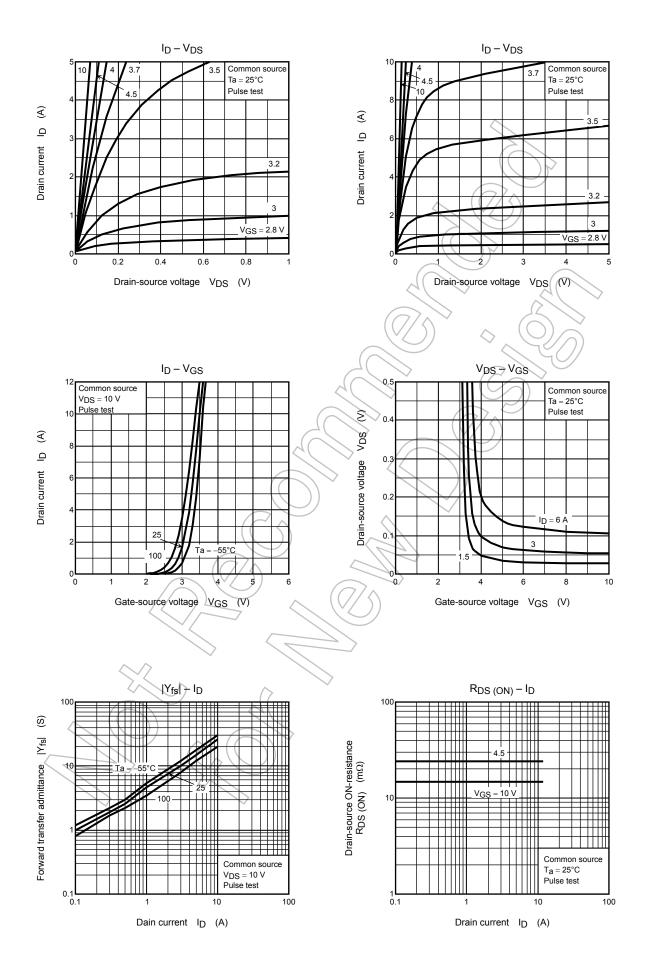
Electrical Characteristics (Ta = 25°C)

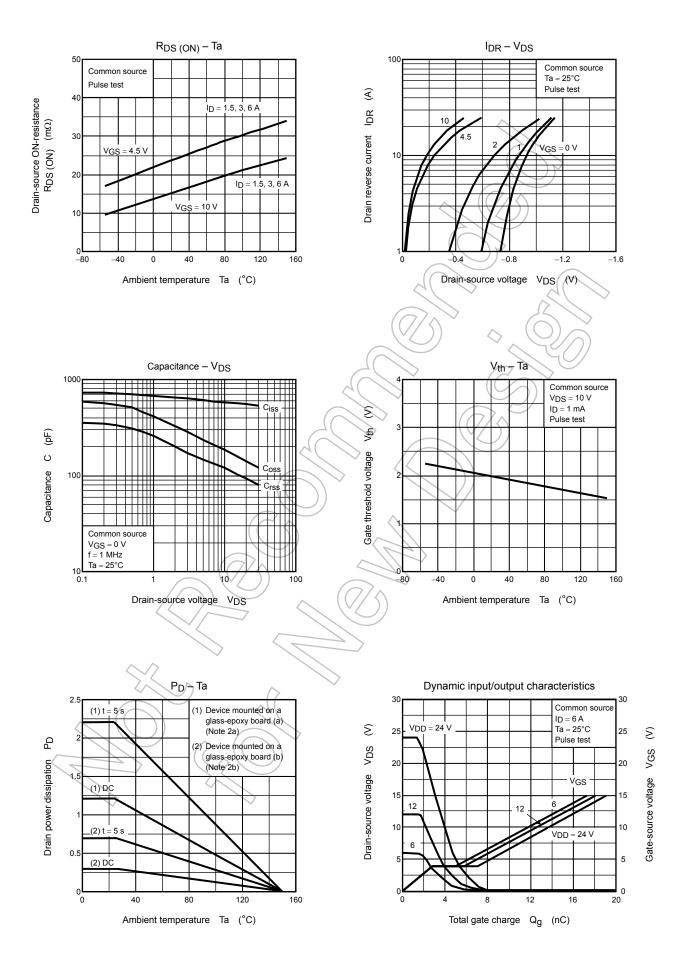
Ch	aracteristics	Symbol	Test Condition	Min Typ. Max		Max	Unit
Gate leakage cui	rrent	I <sub>GSS</sub>	$V_{GS}$ = ± 20 V, $V_{DS}$ = 0 V		_	±100	nA
Drain cut-off curr	ent	I <sub>DSS</sub>	$V_{DS} = 30 \text{ V}, \text{ V}_{GS} = 0 \text{ V}$			10	μA
Drain-source breakdown voltage		V (BR) DSS	$I_D = 10 \text{ mA}, V_{GS} = 0 \text{ V}$	30			V
Dialii-source bre	akuown vollage	V (BR) DSX	$I_D = 10 \text{ mA}, V_{GS} = -20 \text{ V}$	10	_	_	v
Gate threshold v	oltage	V <sub>th</sub>	$V_{DS} = 10 \text{ V}, \text{ I}_{D} = 1\text{mA}$	1.3	)}	2.5	V
Drain-source ON-resistance		R <sub>DS (ON)</sub>	$V_{GS} = 4.5 V, I_D = 3 A$		24	32	mΩ
Diam-source ON	-resistance	R <sub>DS (ON)</sub>	V <sub>GS</sub> =10 V, I <sub>D</sub> = 3 A	$\mathcal{A}$	16	20	1115.2
Forward transfer admittance		Y <sub>fs</sub>	V <sub>DS</sub> = 10 V, I <sub>D</sub> = 3 A	5	10		S
Input capacitance		C <sub>iss</sub>		_	640		
Reverse transfer capacitance		C <sub>rss</sub>	$V_{DS} = 10 \text{ V}, V_{GS} = 0 \text{ V}, f = 1 \text{ MHz}$		125	1	pF
Output capacitance		C <sub>oss</sub>		_	185	$\searrow$	
Switching time	Rise time	tr	$V_{GS} \stackrel{10}{_{0}} \bigvee \qquad I_{D} \stackrel{I_{D}}{=} 3 A$	-((	5.8	>_	
	Turn-on time	t <sub>on</sub>			12		
	Fall time	t <sub>f</sub>		$\mathcal{A}$	8		ns
	Turn-off time	t <sub>off</sub>	$V_{DD} \approx 15 \text{ V}$ Duty $\leq 1\%$ , t <sub>w</sub> = 10 µs	) –	24.5	_	
Total gate charge (gate-source plus gate-drain)		Qg		_	14		nC
Gate-source charge 1		Q <sub>gs 1</sub>	$V_{DD} \approx 24 \text{ V}, \text{ V}_{GS} = 10 \text{ V}, \text{ I}_{D} = 6 \text{ A}$		2.7		
Gate-drain ("miller") charge		Qgd		—	4.2	_	

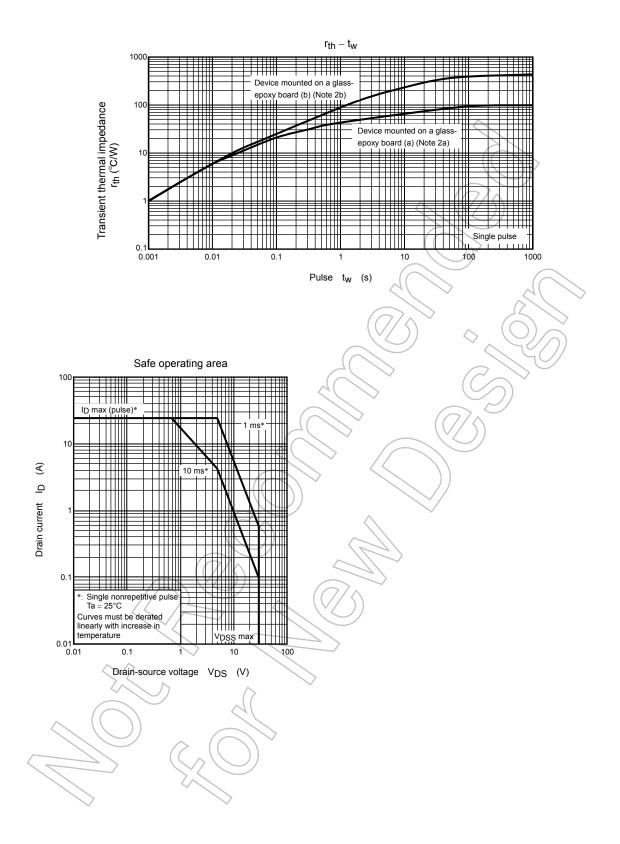
## Source-Drain Ratings and Characteristics (Ta = 25°C)

Charac	teristics	Symbol	Test Condition	Min	Тур.	Max	Unit
Drain reverse current	Pulse (Note 1)	IDRP		_	_	24	А
Forward voltage	(diode)	VDSF	$J_{DR} = 6 A, V_{GS} = 0 V$			- 1.2	V

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